

9. (Twice Amended) A SiGe heterojunction bipolar transistor comprising:

a semiconductor substrate having a collector and subcollector region located therein, wherein said collector is located between isolation regions that are also present in the substrate;

a SiGe layer atop said substrate, said SiGe layer including polycrystalline Si regions positioned above said isolation regions and a SiGe base region located above said collector and subcollector regions;

a patterned insulator layer atop said SiGe base region, said patterned insulator having an opening therein;

an emitter located on said patterned insulator layer and in contact with said SiGe base region through said opening, said emitter, said patterned insulator layer and said SiGe base region each having exposed sidewalls;

a conformal passivation layer positioned on said exposed sidewalls of said emitter, said patterned insulator layer and a portion of said SiGe base region; and

silicide regions located on exposed portions of said SiGe layer, including portions of said SiGe base region, and said emitter not covered by said conformal passivation layer.

REMARKS

Favorable reconsideration and allowance of the claims of the present application are respectfully requested.

Before addressing the specific grounds of rejection raised in the present Office Action, applicants have amended Claim 9 in the manner indicated supra. Specifically, applicants have